# XN01113 (XN1113)

### Silicon PNP epitaxial planar type

For switching/digital circuits

#### Features

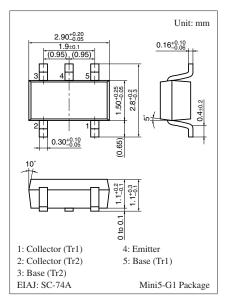
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• UNR2113 (UN2113) × 2

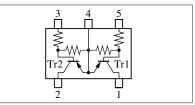
Parameter	Symbol	Symbol Rating					
Collector-base voltage (Emitter open)	nitter open) V <sub>CBO</sub> -50		V				
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V				
Collector current	I <sub>C</sub>	-100	mA				
Total power dissipation	P <sub>T</sub>	300	mW				
Junction temperature	Tj	150	°C				
Storage temperature	T <sub>stg</sub>	-55 to +150	°C				

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$



#### Marking Symbol: 7L

#### Internal Connection



Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -6 V, I_C = 0$			- 0.1	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80			
h <sub>FE</sub> Ratio *	h <sub>FE(Small</sub>	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		_
	/Large)					
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{CC} = -5 \text{ V},  \text{V}_{\text{B}} = -3.5  \text{V},  \text{R}_{\text{L}} = 1  \text{k} \Omega$			- 0.2	V
Input resistance	R <sub>1</sub>		-30%	47	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.8	1.0	1.2	
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

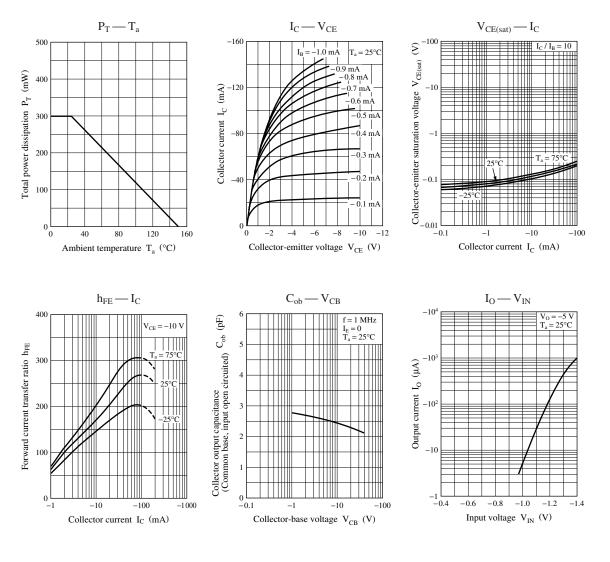
Electrical Characteristics  $T_a = 25^{\circ}C \pm 3^{\circ}C$ 

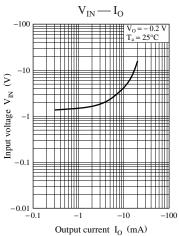
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. \*: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.

#### XN01113







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